



Potential Ion Gate using GEM: experiment and simulation

Philippe Gros
Saga University, Japan



Outline

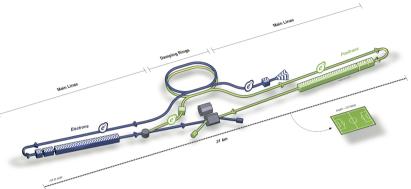


- A TPC for ILC
 - Structure
 - Ion backflow and gate issue
- Ion gating with GEM
 - Concept
 - Experiment
 - Simulation results
- Conclusions and outlook



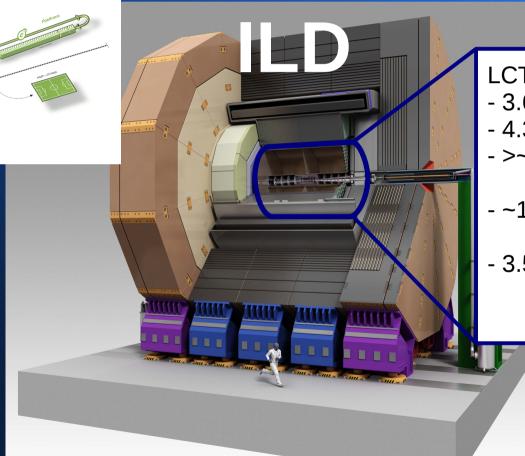
A TPC for ILD@ILC





<u>ILC</u>

- ~31km long
- ~16,000 SCRF cavities
- 250-500GeV e⁺e⁻ upgrade 1TeV
- polarised beams
- 1ms train (~3000 bunch) every 200ms
- 2 Detectors (ILD, SiD)Push-pull
- Japan?
- start 2025???



LCTPC:

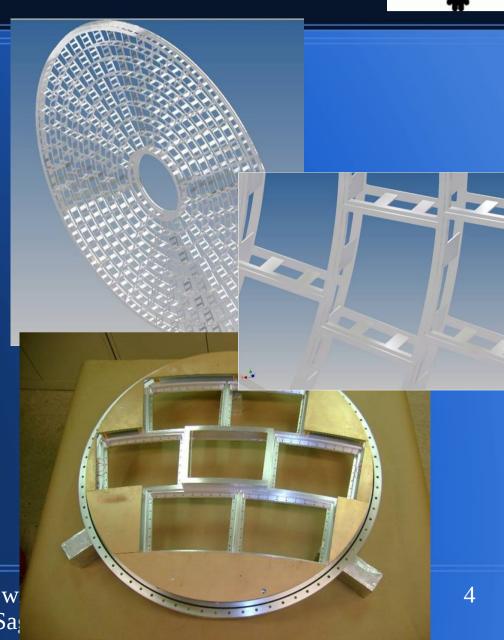
- 3.6m diameter
- 4.3m long
- >~200 points per track
- ~100μm space resolution (rφ)
- 3.5T B-field



Readout plane MPGD modules



- Modular structure
- Minimises dead angles
- Tests with 7 small modules
 - -~20x20cm²
 - GEM or Micromegas





Ion back flow in LCTPC



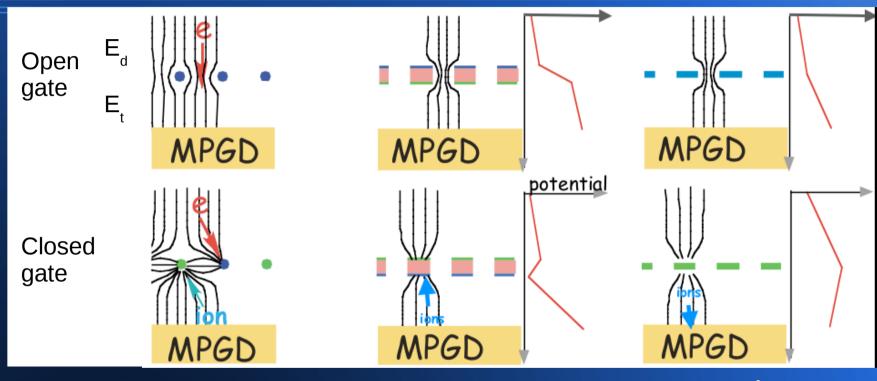
- ILC beam expected to produce large pair background from beamstrahlung
- Simulations by D. Arai, K. Fujii and reproduced by T. Krautscheid
- Simulations show that the positive ions in the TPC will produce non negligible distortions
 - from primary ions: ~8 µm (cannot be avoided)
 - from amplification: ~20BFR μm (back flow rate)

A gating system is necessary



Gating options





Wires

- + Known technology, local E change
- Directional, wire tension, ExB, structure

<u>GEM</u>

- + Symmetry, local E change
- Electron transmission

<u>Mesh</u>

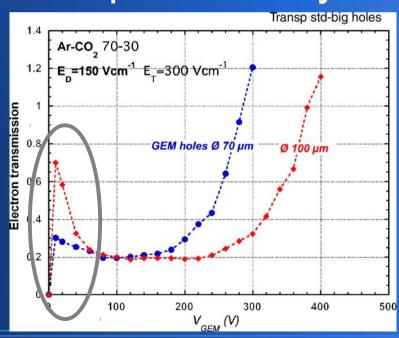
- + Symmetry, simplicity
- Electron transmission, global E change



GEM gate idea



- Suggested in 2006 by Sauli
 - F.Sauli, L.Ropelewski, P.Everaerts NIM A560(2006)269-277
- Transparency peak observed experimentally
 - > Geometrical aperture
 - Relatively high GEM voltage





Simulation

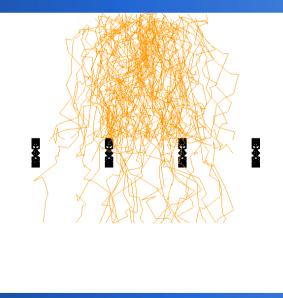


Garfield++

- microscopic description
- gas cross-sections calculated with Magboltz
- Field description from ANSYS®

ANSYS

- Finite elements field calculation
- meshing with curved tetrahedra

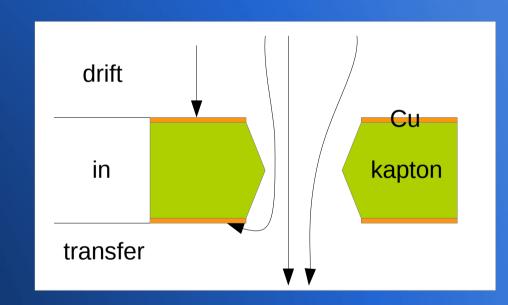




Definitions



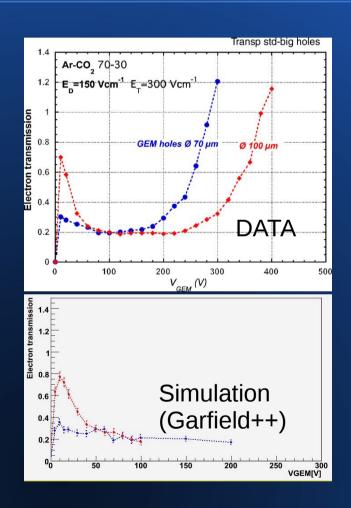
- Collection efficiency
 - $coll = N_{in} / N_{drift}$
- Extraction efficiency
 - extr = $N_{transfer} / N_{in}$
- Transmission
 - $-T = N_{transfer} / N_{drift} = coll x extr$

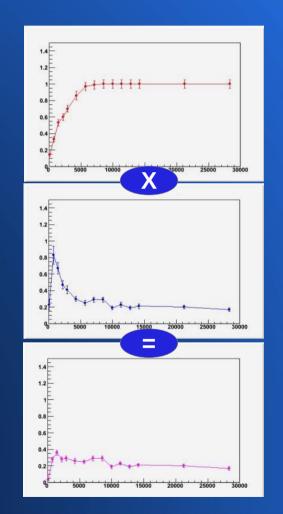


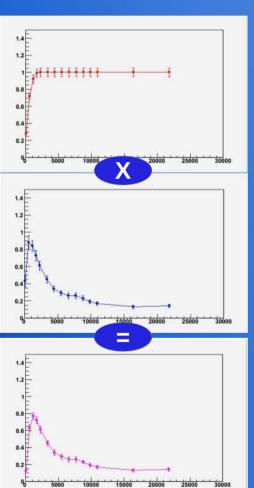


Simulation of Sauli's experiment







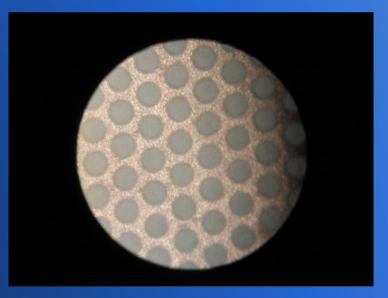




Experiments with a thin GEM gate (14µm)



- A specific GEM gate was produced
- Thin GEM
 - 14µm kapton, 1µm copper
- Relatively large aperture
 - 90 µm diameter
 - 140 µm pitch
 - => 37% geometrical aperture



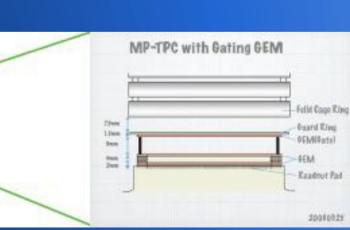


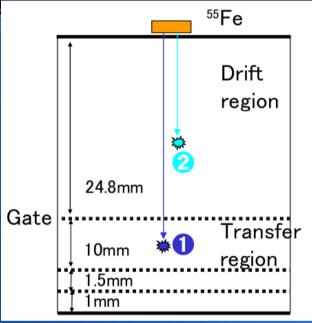
GEM gate experiments



- Transparency measurement
 - Compare the signal create before and after the gate
 - Systematic effects cancel out
- Space resolution
 - 1T magnet
 - Cosmic rays
 - Evaluate N effective







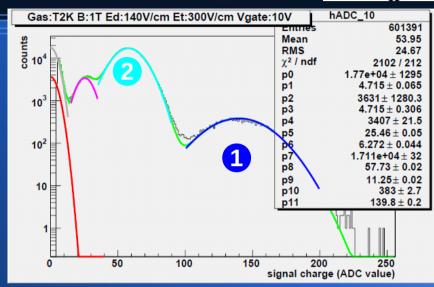


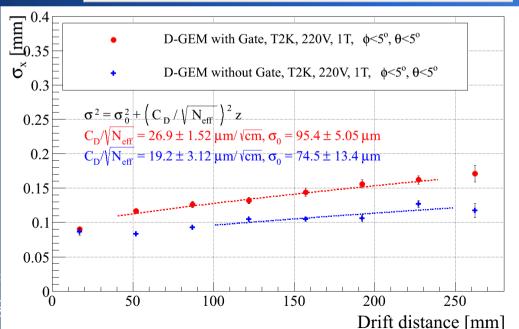
Experiment Result



Transparency ~50% at B=1T

Consistent with 50% transparency



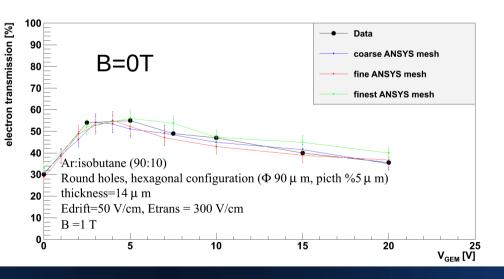


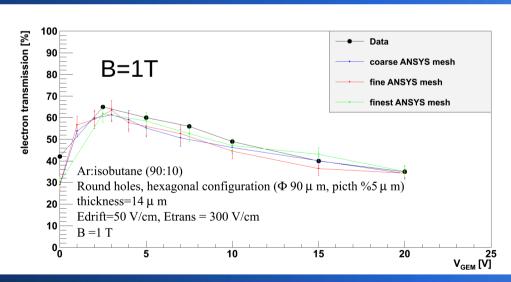


Simulation



- Using Garfield++ and ANSYS
- Reproduces the experimental transparency measurement very well



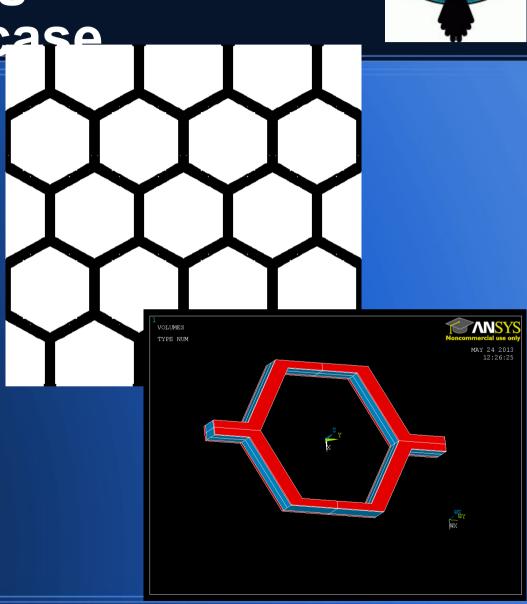




Large aperture Simulating an extreme



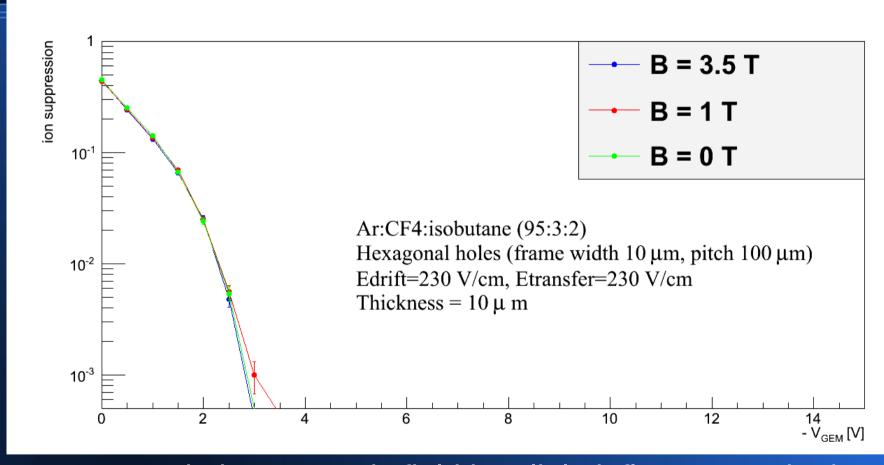
- Maximize the aperture
- Honeycomb structure
- 10µm wide, 100µm pitch
 - 81% aperture
 - difficult to build





Closing the gate





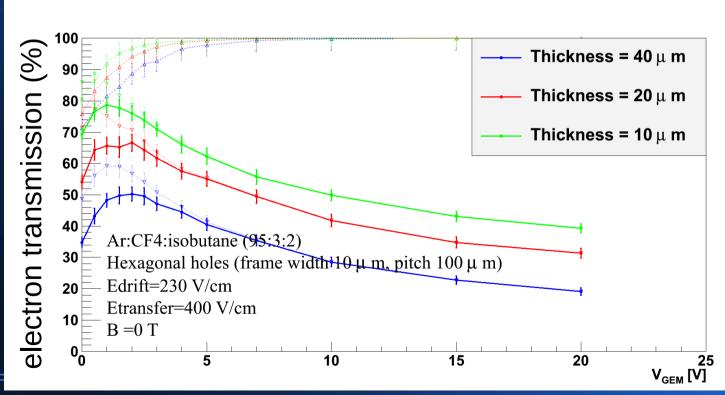
As expected, the magnetic field has little influence on the ions A GEM voltage above **3V** already gives enough ion suppression.



First result



- Without magnetic field
- Good transparency requires extreme conditions

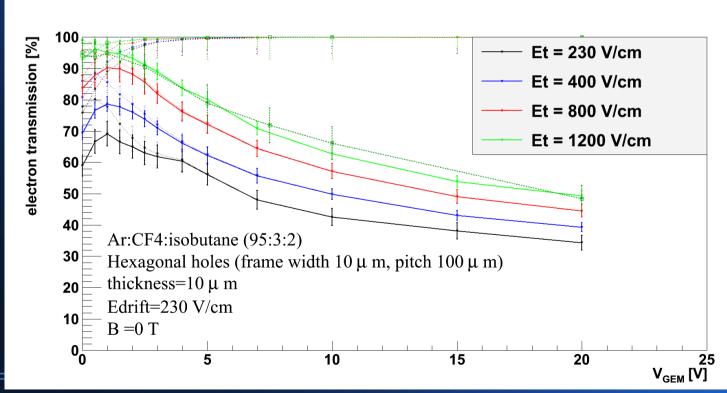




First result



- Without magnetic field
- Good transparency requires extreme conditions

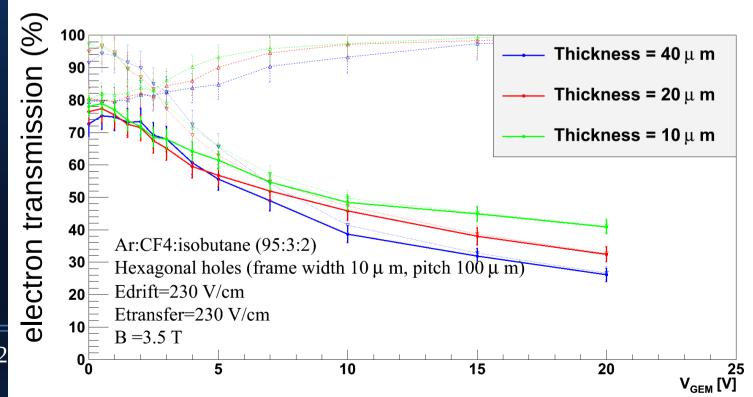




With 3.5T B field



- ωτ~10 => the electrons follow B, little diffusion
- Electric field and thickness have little influence
- Geometric transparency (81%)





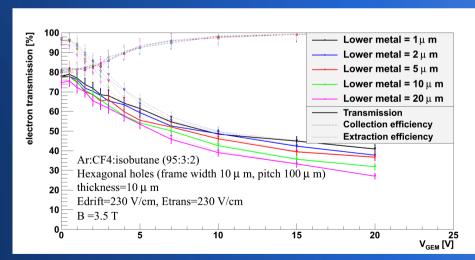
Conclusion and outlook

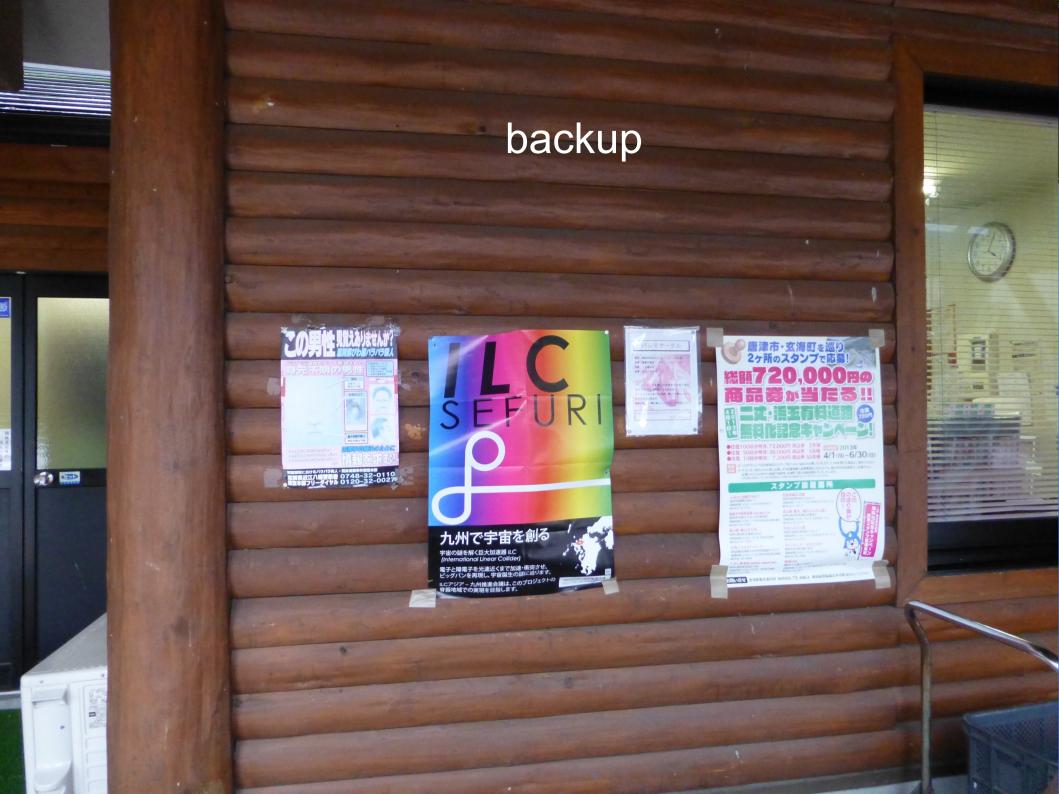


 Garfield++ simulations give a good description of GEM gate performance

 In high B field, geometrical aperture becomes the key parameter

- Difficulties are mechanical
 - How to make thin structure
 - Maybe improved with thicker metal?

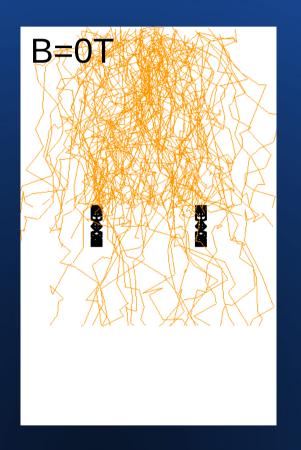


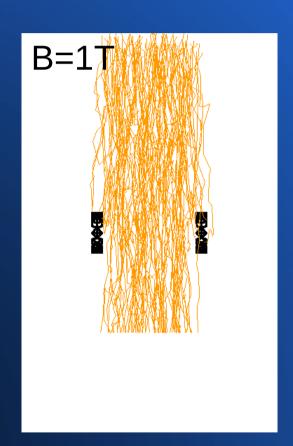




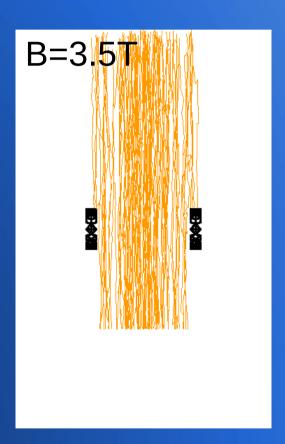
Effect of B field







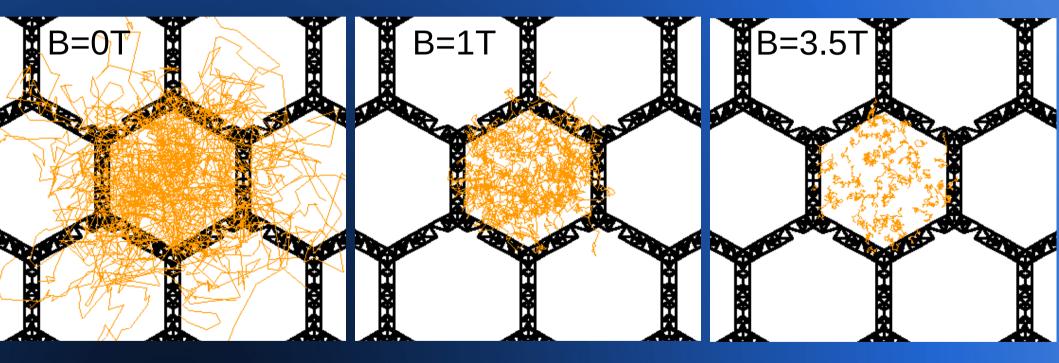
Ion gating with GEM





Effect of B field

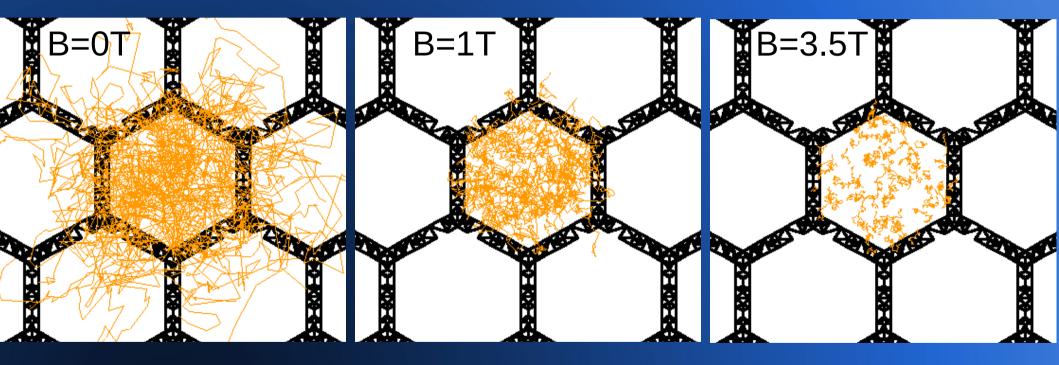






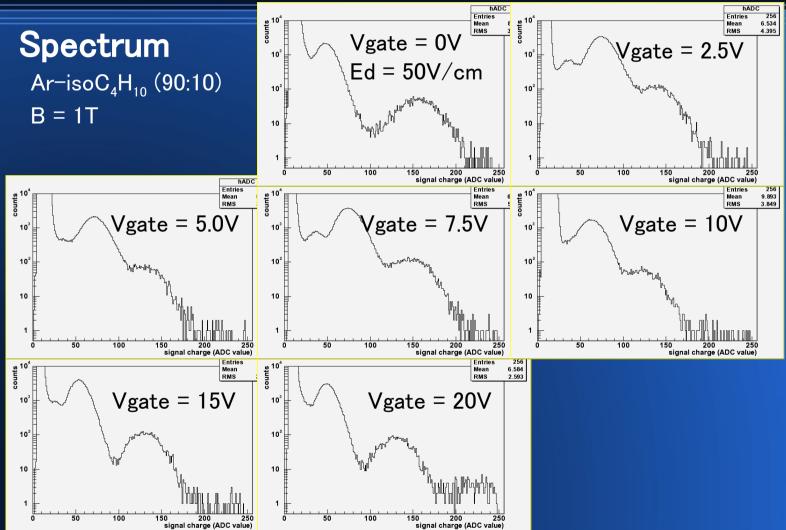
Effect of B field













Wire gate



- Well known technology
- Difficult to adapt to the module structure
- Possible effects of B field
 - => Radial wires
 - No radial support structure: minimises dead regions
 - ExB in the wire direction => minimises distrotions



Radial wire gate prototype







Status



- 3 prototypes were built
 - 30µm wires, 2mm pitch
 - spot welded on stainless steel frame
 - only one potential: no alternate potential closed gate scheme
- Could not be tested yet
 - small design error has to be fixed
- Planned test with laser at KEK
- Needs to be tested in B field